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				•	APPLICANT Tetsuzo UEDA, et al.					
		(PT	O-1449)		FILING DATE March 30, 2004	GROUP 2811				
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EXAMINER /Sara Crane/					DATE CONSIDERED 10/16/2006					

^{*}EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

1 Applicant's unique citation designation number (optional). 2 Applicant is to place a check mark here if English language Translation is attached.

SHEET 1 OF 1

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